BATOP
o p t o e l e c t r o n i c s

SAM™ data sheet SAM-800-1-5ps-x, λ = 800 nm

Laser wavelength	λ = 800 nm
High reflection band	λ = 780 .. 820 nm
Low intensity reflectivity	R_0 = 97.5 %
Scattering loss	L = 1.5 %
Absorbance	A_0 = 1 %
Modulation depth	ΔR = 0.6 %
Saturation fluence	Φ_{sat} = 100 µJ/cm^2
Relaxation time constant	τ ~ 5 ps
Damage threshold	Φ = 4 mJ/cm^2
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 µm
Protection	The SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm $\varnothing$
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm $\varnothing$
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm $\varnothing$
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm $\varnothing$
x = 25.0 w	soldered on a water cooled Cu-cylinder with 25.0 mm $\varnothing$
x = FC	mounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance and dispersion (GDD)

SAM-800-1-5ps-x   wafer 1088-l

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